Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical device, comprising:

a substrate;

a pixel electrode;

a scanning line including a main portion and a gate electrode;

a data line crossing the scanning line; and

a transistor disposed at least in an intersection between the data line and the scanning line where the data line and the scanning line cross, the transistor including the gate electrode and a semiconductor layer, ~~wherein~~

the gate electrode is disposed outside the intersection where the data line and scanning line cross,

the semiconductor layer ~~comprises~~ includes a source region that is connected to the pixel electrode through a contact hole, a drain region that is connected to the data line through a second contact hole, a channel region disposed under the gate electrode, and a semiconductor portion protruding out of the channel region and not being covered with the gate electrode, and

the semiconductor portion protruding out of the channel region and not being covered with the gate electrode only connects directly with the channel region.

2. (Previously Presented) The electro-optical device according to claim 1, the semiconductor layer forming the transistor comprising monocrystalline silicon.

3. (Previously Presented) The electro-optical device according to claim 1, the semiconductor layer forming the transistor comprising polycrystalline silicon.

4. (Original) The electro-optical device according to claim 1, the substrate being an insulative substance.

5. (Original) The electro-optical device according to claim 1, the substrate being a quartz substrate.

6. (Original) The electro-optical device according to claim 1, the substrate being a glass substrate.

7. (Original) The electro-optical device according to claim 1, the substrate being a first substrate provided with semiconductor layers, the electro-optical device further comprising:

a second substrate disposed opposing a surface of the first substrate; and

liquid crystals sandwiched by the first substrate and the second substrate, and driven by transistor elements formed on the semiconductor layers.

8. (Previously Presented) An electronic equipment, comprising:

a light source;

the electro-optical device according to claim 1 that modulates, in accordance with image information, an incident light emitted by the light source; and

a projection system that projects a light modulated by the electro-optical device.

9-19. (Canceled)

20. (Previously Presented) the electro-optical device according to claim 1, the semiconductor portion protruding in a direction in which the scanning line extends.

21. (Previously Presented) The electro-optical device according to claim 1, the gate electrode has two parts protruding out of the semiconductor layer, and the source region or the drain region being disposed between the two parts.

22-23. (Canceled)

24. (Currently Amended) An electro-optical device, comprising:

a substrate;

a plurality of pixel electrodes;

a plurality of scanning lines, each of the plurality of scanning lines including a gate electrode;

a plurality of data lines, one of the data lines crossing one of the plurality of scanning line forming an intersection; and

a plurality of transistors, each one of the plurality of transistors disposed at least in the intersections between the plurality of data lines and the plurality of scanning lines where the plurality of data lines and the plurality of scanning lines cross, each of the plurality of transistors including the gate electrode and a semiconductor layer, ~~wherein~~

the gate electrode is disposed outside the intersections where the data line and the scanning line cross,

the semiconductor layer ~~comprises~~ includes a source region that is connected to one of the plurality of pixel electrodes through a contact hole, a drain region that is connected to the data line through a second contact hole, a channel region disposed under the gate electrode, and a semiconductor portion protruding out of the channel region and not being covered with the gate electrode, and

the semiconductor portion protruding out of the channel region and not being covered with the gate electrode only ~~corrects~~ connects directly with the channel region.